



N-Channel Silicon MOSFET **CPH6613**—General-Purpose Switching Device **Applications**

Features

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- 1.8V drive.
- Composite type with two MOSFETs contained in a single package facilitating high-density mounting.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	VGSS		±12	V
Drain Current (DC)	۱D		2.5	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	10	А
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm)1unit	0.9	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0			1	μΑ
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VDS=0			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =1.5A	2.0	3.4		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=1.5A, VGS=4V		70	95	mΩ
	R _{DS} (on)2	ID=0.8A, VGS=2.5V		95	135	mΩ
	RDS(on)3	ID=0.4A, VGS=1.8V		130	198	mΩ
Input Capacitance	Ciss	VDS=10V, f=1MHz		270		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		60		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		53		pF

Marking : FZ

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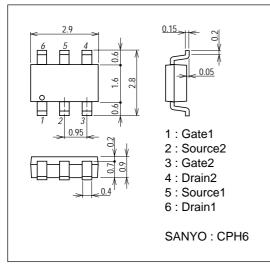
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Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		10		ns
Rise Time	tr	See specified Test Circuit.		44		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		37		ns
Fall Time	tf	See specified Test Circuit.		38		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =4V, I _D =2.5A		4.0		nC
Gate-to-Source Charge	Qgs	VDS=10V, VGS=4V, ID=2.5A		0.6		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =4V, I _D =2.5A		1.9		nC
Diode Forward Voltage	VSD	IS=2.5A, VGS=0		0.91	1.2	V

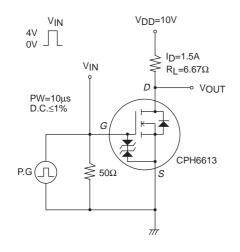
Package Dimensions

unit : mm

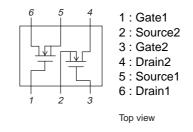
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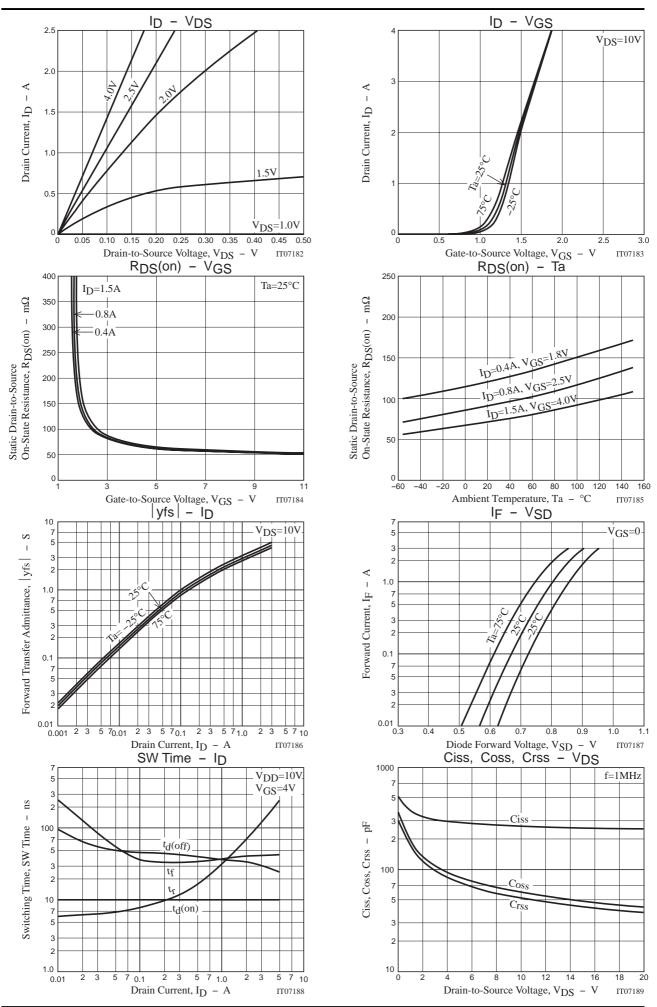


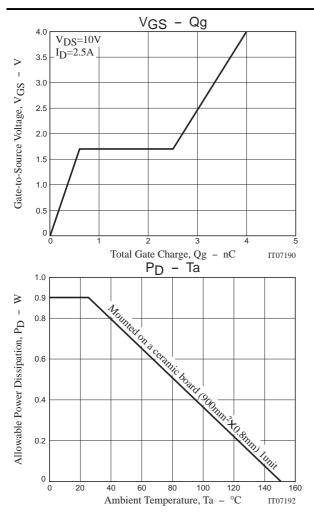
Switching Time Test Circuit

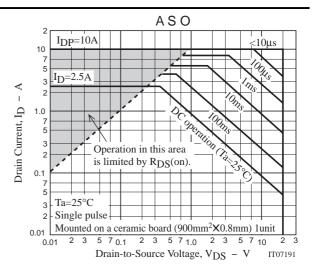


Electrical Connection









Note on usage : Since the CPH6613 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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